



PJ4N3KDW

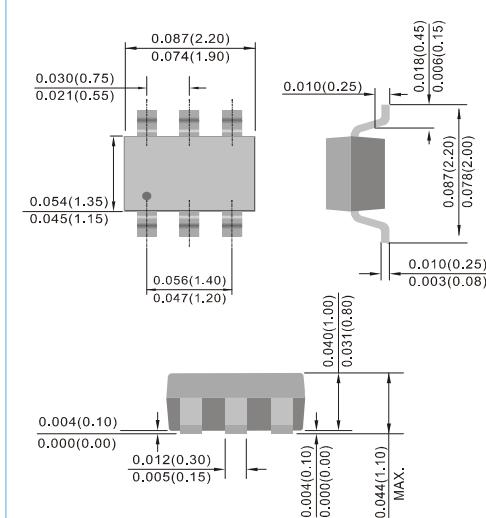
30V Dual N-Channel Enhancement Mode MOSFET - ESD Protected

FEATURES

- $R_{DS(ON)}$, V_{GS} @2.5V, I_{DS} @1mA=7.0 Ω
- $R_{DS(ON)}$, V_{GS} @4.0V, I_{DS} @10mA=5.0 Ω
- Advanced Trench Process Technology
- High Density Cell Design For Ultra Low On-Resistance
- The MOSFET elements are independent, eliminating interference
- Mounting cost and area can be cut in half
- Very Low Leakage Current In Off Condition
- Specially Designed for Battery Operated Systems, Solid-State Relays
Drivers : Relays, Displays, Lamps, Solenoids, Memories, etc.
- Low voltage drive (2.5V) makes this device ideal for portable equipment
- ESD Protected 2kV HBM
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Green molding compound as per IEC61249 Std. . (Halogen Free)

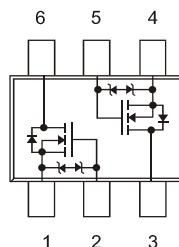
SOT-363

Unit : inch(mm)



MECHANICAL DATA

- Case: SOT-363 Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Weight: 0.0002 ounces, 0.006 grams
- Marking : 4N3



Absolute Maximum Ratings ($T_A=25^\circ\text{C}$)

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	100	mA
Pulsed Drain Current ⁽¹⁾	I_{DM}	800	mA
Maximum power Dissipation $T_A=25^\circ\text{C}$ $T_A=75^\circ\text{C}$	P_D	200 120	mW
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to + 150	°C
Junction-to Ambient Thermal Resistance (PCB mounted) ⁽²⁾	$R_{\theta JA}$	625	°C/W

Note: 1. Maximum DC current limited by the package

2. Surface mounted on FR4 board, $t \leq 5$ sec



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ELECTRICAL CHARACTERISTICS ($T_A=25^\circ C$)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Units
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=10\mu A$	30	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=3.0V, I_D=100\mu A$	0.8	-	1.5	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=2.5V, I_D=1mA$	-	-	7.0	Ω
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=4.0V, I_D=10mA$	-	-	5.0	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$	-	-	1	μA
Gate Body Leakage	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	5	μA
Forward Transconductance	g_{fs}	$V_{DS}=3V, I_D=10mA$	10	-	-	mS
Diode Forward Voltage	V_{SD}	$I_s=115mA, V_{GS}=0V$	-	0.78	1.3	V
Dynamic						
Total Gate Charge	Q_g	$V_{DS}=15V, I_D=10mA$ $V_{GS}=4.5V$	-	-	0.8	nC
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=5V, R_L=500\Omega$ $I_D=10mA, V_{GEN}=5V$ $R_G=10\Omega$	-	30	35	ns
Rise Time	t_r		-	8.5	12	
Turn-Off Delay Time	$t_{d(off)}$		-	84	100	
Fall time	t_f		-	32	40	
Input Capacitance	C_{iss}	$V_{DS}=5V, V_{GS}=0V$ $f=1.0MHz$	-	25	35	pF
Output Capacitance	C_{oss}		-	8	12	
Reverse Transfer Capacitance	C_{rss}		-	2.5	5	



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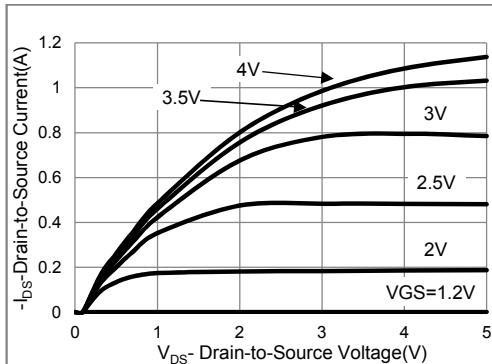


Fig.1 On-Region Characteristics.

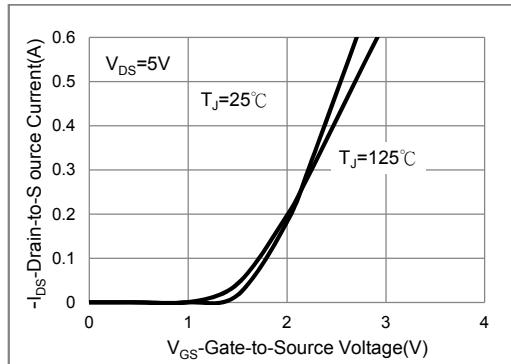


Fig.2 Transfer Characteristics

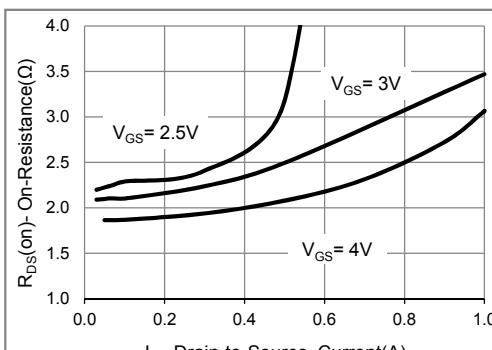


Fig.3 On-Resistance vs. Drain current

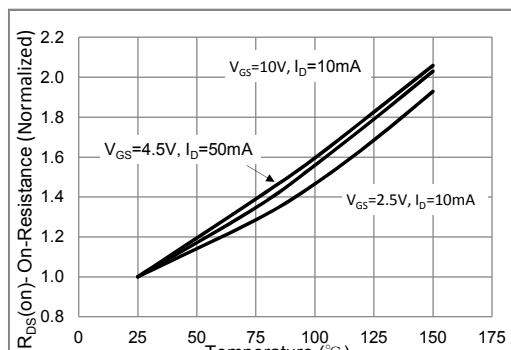


Fig.4 On-Resistance vs. Junction

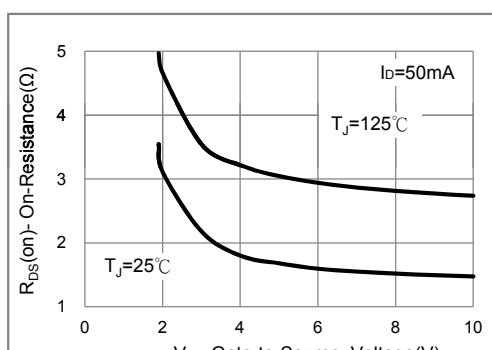


Fig.5 On-Resistance Variation with VGS.

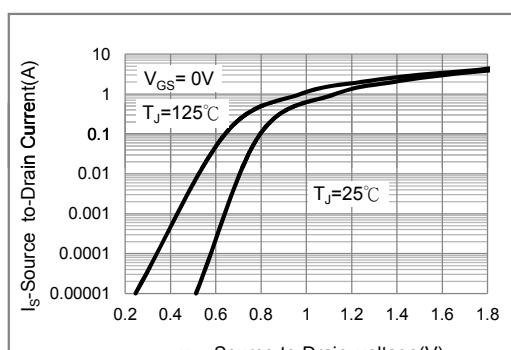


Fig.6 Body Diode Characteristics

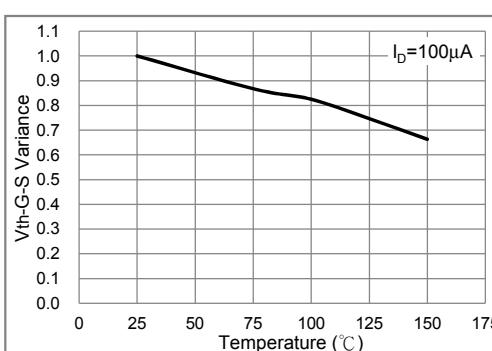


Fig.7 Threshold Voltage Variation with Temperature

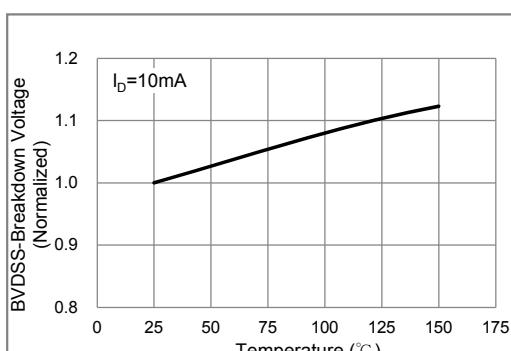
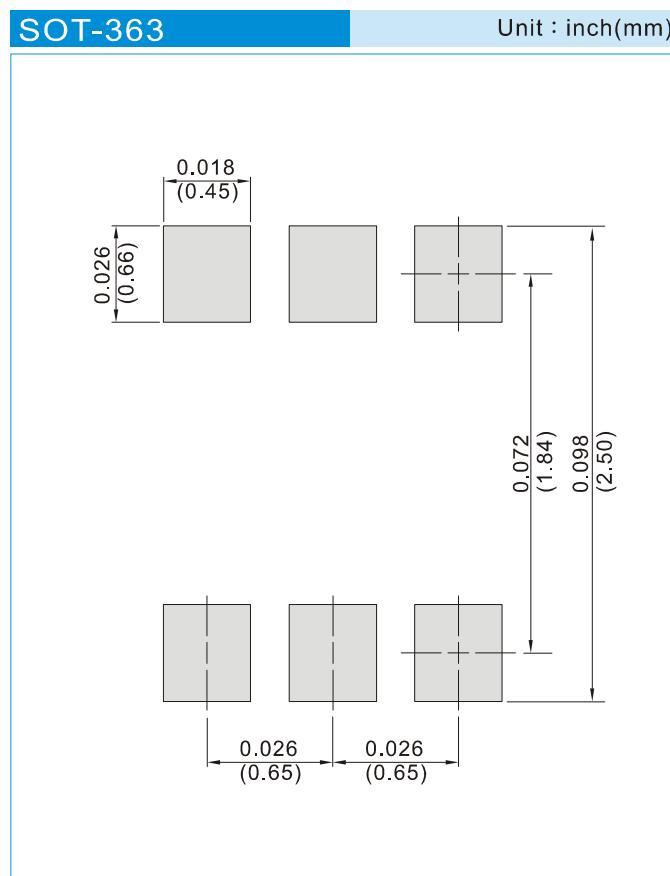


Fig.8 Breakdown Voltage Variation vs. Temperature



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MOUNTING PAD LAYOUT



ORDER INFORMATION

- Packing information
 - T/R - 10K per 13" plastic Reel
 - T/R - 3K per 7" plastic Reel



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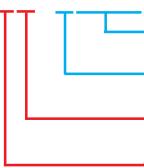
Part No_packing code_Version

PJ4N3KDW_R1_00001

PJ4N3KDW_R2_00001

For example :

RB500V-40_R2_00001

- | | |
|----------|--|
| Part No. |  <ul style="list-style-type: none"> • Serial number • Version code means HF • Packing size code means 13" • Packing type means T/R |
|----------|--|

Packing Code XX				Version Code XXXXX		
Packing type	1 st Code	Packing size code	2 nd Code	HF or RoHS	1 st Code	2 nd ~5 th Code
Tape and Ammunition Box (T/B)	A	N/A	0	HF	0	serial number
Tape and Reel (T/R)	R	7"	1	RoHS	1	serial number
Bulk Packing (B/P)	B	13"	2			
Tube Packing (T/P)	T	26mm	X			
Tape and Reel (Right Oriented) (TRR)	S	52mm	Y			
Tape and Reel (Left Oriented) (TRL)	L	PANASERT T/B CATHODE UP (PBCU)	U			
FORMING	F	PANASERT T/B CATHODE DOWN (PBCD)	D			



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